Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	_. 436	@ad<="20011004" and power with MOSFET and voltage with sustain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:20
L2	436	@ad<="20011004" and power with MOSFET and (voltage with sustain\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:20
L3	259	@ad<="20011004" and "power MOSFET" and (voltage with sustain\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:20
L4	29	@ad<="20011004" and "power MOSFET" same (voltage with sustain\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:29
L5	1140	@ad<="20011004" and (257/330-332).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:22
L6	539	@ad<="20011004" and (257/339). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:23
L7	190	@ad<="20011004" and (257/333). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:23
L8	948	@ad<="20011004" and (257/328-329) ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:25
Ù9	2	("5,216,275").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/09 08:26
L11	. 98	@ad<="20011004" and "power MOSFET" same voltage with (sustain\$3 or drift)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 08:30

S1	65	(438/212).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/02/21 14:21
S2	65	(("438/212").CCLS.) and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/11 13:21
S3	3	("5216275").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/02/08 09:29
S4	9891	"438"/\$.ccls. and 'trench'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/08 11:03
S5	228088	"257"/\$.ccls. or "438"/\$.ccls. and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/08 15:36
S6		("257"/\$.ccls. or "438"/\$.ccls. and @ad<="20011004") and 'terraced trench'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/08 11:09
S7	9	(("5072266") or ("5541425") or ("5866931")) PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/02/08 12:36
S8	228088	"257"/\$.ccls. or "438"/\$.ccls. and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/08 15:41
S9	1	("257"/\$.ccls. or "438"/\$.ccls. and @ad<="20011004") and 'high voltage vertical MOSFET'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/08 15:44
S10	5	("257"/\$.ccls. or "438"/\$.ccls. and @ad<="20011004") and 'high voltage vertical channel'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/08 15:47

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S11	1475	((438/270) or (257/493)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF ,	2002/02/11 13:10
S12	65	(("438/212").CCLS.) and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/11 14:28
S13	411	((438/211) or (438/268)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/02/11 14:28
S14	1137	((257/330-332) or (257/329)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/02/21 12:45
S15	459	(257/328) CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/02/21 12:21
S16	1137	((257/330-332) or (257/329)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/09 08:22
S17	3	("4893160").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/02/21 13:17
S18	1952	((438/259) or (438/270-271) or (438/212) or (438/589)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/02/21 13:43
S19	3	("5637898").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/02/21 13:45

S20	4	'voltage sustaining layer'	US-PGPUB; USPAT;	OR	ON	2006/03/09 08:18
			EPO; JPO; DERWENT; IBM_TDB			
S21	593	'semiconductor power device'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 15:51
S22	23	'p doping' with 'bottom'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 15:41
S23	22	@ad<="20011004" and 'p doping' with 'bottom'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 16:18
S24	2	("6194741").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/07/23 15:46
S25	. 1	"4116720".PN.	USPAT	OR	OFF	2002/07/23 15:47
S26	1	"5378914".PN.	USPAT	OR	OFF	2002/07/23 15:47
S27	1	"5378914".PN.	USPAT	OR	OFF	2002/07/23 15:48
S28	1	"5770878".PN.	USPAT	OR	OFF	2002/07/23 15:48
S29	1	"5831288".PN.	USPAT	OR	OFF	2002/07/23 15:48
S30	1	"5915180".PN.	USPAT	OR	OFF	2002/07/23 15:49
S31	1	"6020600".PN.	USPAT	OR	OFF	2002/07/23 15:49
S32	566	@ad<="20011004" and 'semiconductor power device'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/11 12:38
S33	2943	((438/212) or (438/270) or (438/493) or (438/211) or (438/259) or (438/271) or (438/589) or (438/284) or (438/286) or (438/931)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/07/23 16:21
S34	2852	(((438/212) or (438/270) or (438/493) or (438/211) or (438/259) or (438/271) or (438/589) or (438/284) or (438/286) or (438/931)). CCLS.) and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 16:22

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S35	1	((((438/212) or (438/270) or (438/493) or (438/211) or (438/259) or (438/271) or (438/589) or (438/284) or (438/286) or (438/105) or (438/931)).CCLS.) and @ad<="20011004") and 'p type doping' with 'bottom'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 16:25
S36	6	((((438/212) or (438/270) or (438/493) or (438/211) or (438/259) or (438/271) or (438/589) or (438/284) or (438/286) or (438/931)). CCLS.) and @ad<="20011004") and 'bottom' near 'doping'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 16:25
S37		@d<="20011004" and 'UMOSFET'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 16:45
S38	. 108	UMOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/11 12:44
S39	3	("4754310").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/07/24 09:01
S40	271	@ad<="20011004" and 'power device' and 'sustaining'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/11 14:19
S41	397	@ad<="20011004" and (438/268). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/11 13:39
S42	438	@ad<="20011004" and (438/296). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/11 13:40
S43	242	@ad<="20011004" and (438/298). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR 	ON	2003/03/11 13:40
S44	208	@ad<="20011004" and (438/433-434).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/11 13:40

S45	525	@ad<="20011004" and (257/328). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/11 13:41
S46	420	@ad<="20011004" and (257/329). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/11 13:41
S47	680	@ad<="20011004" and (257/330). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/11 13:42
S48	152	@ad<="20011004" and (257/334). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/11 13:42
S49	437	@ad<="20011004" and 'power device' and 'drift region'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/11 15:02
S50	0	North-carolina-state as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/11 15:03
S51	57	North adj1 Carolina adj1 State.as. and 'power device'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/11 15:05
S52	4	(("5953621") or ("6097076")) PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/13 09:55
S53	2	("6380569").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/13 09:56
S54	2	"20040097028"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 15:56

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S55	2	("6465304").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/08 15:57
S56	2	("6649477").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR ,	OFF	2006/03/08 15:57
S58	0	@ad<="20011004" and blanchard-richard in and "power semiconductor"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 16:36
S59	28	@ad<="20011004" and blanchard with richard and "power semiconductor"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 16:23
S60	131	@ad<="20011004" and "blanchard" and "power semiconductor"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 16:23
S61	51	"blanchard richard" and "power semiconductor"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 16:24
S62	1	"20020135014".PN.	US-PGPUB	OR	ON	2006/03/08 16:27
S63	1	"20020132405".PN.	US-PGPUB	OR	ON	2006/03/08 16:27
S64	1	"20020123195".PN.	US-PGPUB	OR	ON	2006/03/08 16:27
S65	1	"20020008258".PN.	US-PGPUB	OR	ON	2006/03/08 16:28
S66	1	"20010053568".PN.	US-PGPUB	OR	ON	2006/03/08 16:28
S67	1	"20010046739".PN.	US-PGPUB	OR	ON	2006/03/08 16:28
S68	3	@ad<="20011004" and epitaxial same (Terrac\$2 with Trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 16:37
S69	42	@ad<="20011004" and Terrac\$2 with Trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/08 16:47

S70	2	("6380569").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/08 16:47
S71	1	"4140558".PN.	USPAT; USOCR	OR	ON	2006/03/08 16:57
S72	1	"4419150".PN.	USPAT; USOCR	OR .	ON	2006/03/08 16:58
S73	1	"4569701".PN.	USPAT; USOCR	OR	ON	2006/03/08 16:58
S74	1	"4711017".PN.	USPAT; USOCR	OR	ON	2006/03/08 16:59
S75	1	"4893160".PN.	USPAT; USOCR	OR	ON	2006/03/08 17:00
S76	· 1	"4914058".PN.	USPAT; USOCR	OR	ON	2006/03/08 17:00
S77	1	"5108783".PN.	USPAT; USOCR	OR	ON	2006/03/08 17:01
S78	1	"5216275".PN.	USPAT; USOCR	OR	ON	2006/03/08 17:02
S79	· 1	"6376878".PN.	USPAT; USOCR	OR	ON	2006/03/08 17:02
S80	1	"6475864".PN.	USPAT; USOCR	OR	ON	2006/03/08 17:02
S81	. 1	"6576516".PN.	USPAT; USOCR	OR	ON	2006/03/08 17:03
S82	1	"20010026977".PN.	US-PGPUB	OR	ON	2006/03/08 17:03
S83	1	"20010041400".PN.	US-PGPUB	OR	ON	2006/03/08 17:03
S84	1	"20010036704".PN.	US-PGPUB	OR	ON	2006/03/08 17:04
S85	1	"20010046739".PN.	US-PGPUB	OR	ON	2006/03/08 17:05
S86	1	"20010053568".PN.	US-PGPUB	OR	ON	2006/03/08 17:05
S87	1	"20020008258".PN.	US-PGPUB	OR	ON	2006/03/08 17:06
S88	1	"20020123195".PN.	US-PGPUB	OR	ON	2006/03/08 17:06
S89	1	"20020132405".PN.	US-PGPUB	OR	ON	2006/03/08 17:07
S90	1	"20020135014".PN.	US-PGPUB	OR	ON	2006/03/08 17:07